

NPN RF POWER TRANSISTOR

DESCRIPTION:

The **ASI BLX94A** is a Common Emitter Device Designed for Class A, B and C Amplifier Applications from 50 to 500 MHz.

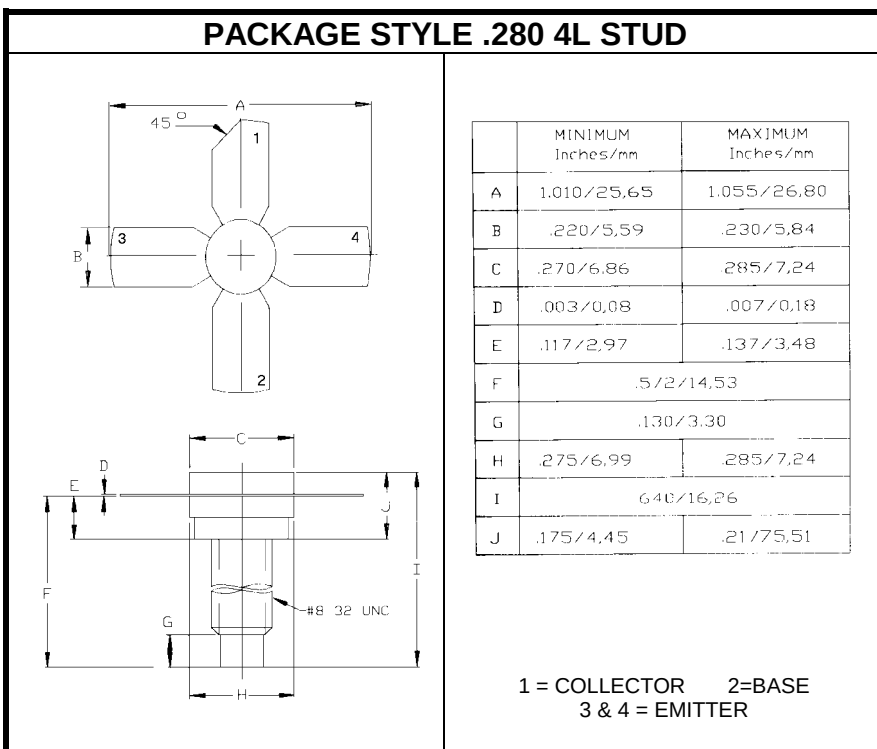
FEATURES INCLUDE:

- High Gain
- Gold Metallization
- Emitter Ballasting

MAXIMUM RATINGS

I_C	2.5 mA
V_{CBO}	65 V
P_{DISS}	60 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	4.0 $^\circ\text{C/W}$

PACKAGE STYLE .280 4L STUD



CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
V_{CES}	$I_C = 25\text{ mA}$	65			V
V_{CEO}	$I_C = 100\text{ mA}$	30			V
V_{BEO}	$I_E = 10\text{ mA}$	4.0			V
I_{CES}	$V_{CE} = 30\text{ V}$			10	mA
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 1.5\text{ A}$	15	50		---
C_{OB}	$V_{CB} = 28\text{ V}$ $f = 1.0\text{ MHz}$		33		pF
P_G η_C	$V_{CE} = 28\text{ V}$ $P_{OUT} = 25\text{ W}$ $f = 470\text{ MHz}$	6.5 55			dB %